Lead (Pb) Free Product – RoHS Compliant

SPECIFICATION OF LED CHIP
C1060-30
[NIR]

1) Commodity Type and Physical Characteristics.

1. Material		InGaAsP/InP	
2. Electrode	Top Side	P (anode) side	: Au Alloy
	Bottom Side	N (cathode) side	: Au Alloy
3. Electrode Pattern			Fig.1
4. Chip Size			Fig.2
5. Chip Thickness			Fig.2
6. Emission Area			Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.08	1.4	V
		If=50mA		1.11	1.5	
Reverse Current	Ir	Vr=3V			10	uA
Power Intensity	Po	If=20mA		1.0		mW
		If=50mA		2.0		
Peak Wavelength	λP	If=20mA		1060		nm
Spectral Radiation Bandwidth	Δλ	If=20mA		45		nm
RiseTime	tr	If=20mA		20		ns
FallTime	tf	If=20mA		20		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.
‡ Power intensity is measured by PD G8370-85.

[Unit: um]

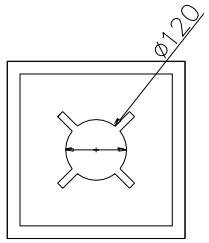

Fig.1 Electrode Pattern

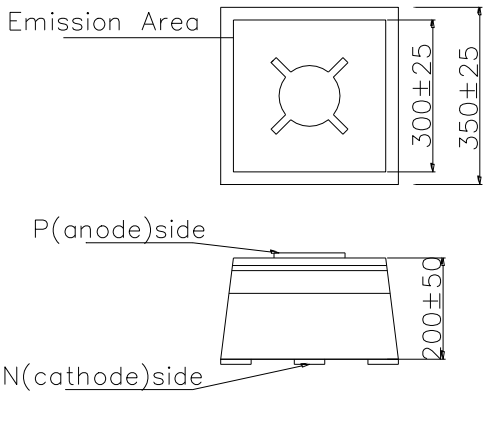

Fig.2 Chip size and Emission Area

Marubeni America Corporation
3945 Freedom Circle, Suite 1000, Santa Clara, CA 95054
408-330-0650 (Ext. 330), 408-330-0655 (FAX), sales@tech-led.com